

TOTAL IONIZING DOSE

TEST REPORT



TRAD/TE/OLH400/XXX1/ESA/YP/1104		Labège, April 30th, 2012
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Issue : 0		
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1 INTRODUCTION

This report includes the test results of OLH400, a High Speed Hermetic Low Input-Current Optocoupler from ISOLINK to evaluate Total Ionizing Dose (TID) effects under ^{60}Co irradiation. Between November 2011 and February 2012, TRAD characterized this device for TID sensitivity at the UCL Facility, Belgium using their Gamma irradiation Facility.

The objectives of the test are:

- to detect and measure the degradation of device parameters as a function of TID,
- to determine if device parameters are within specified limits after exposure to final TID level.

2 DOCUMENTS

2.1 Applicable Documents

AD	1.	ESA contract	N°4000102571/10/NL/AF-Radiation Characterization of Laplace RH optocouplers, sensors and detectors
AD	2.	Irradiation Test Plan	ITP-TE-OLH400-ISO-ESA-1115, Issue 2 dated 21/06/2011

2.2 Reference Documents

RD	1.	Datasheet OLH400	High Speed Hermetic Low Input-Current Optocoupler dated 27/03/2002
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3 DEVICE INFORMATION

3.1 Device description

The OLH400 is a High Speed Hermetic Low Input-Current Optocoupler. The OLH 400 has high current transfer ratio at very low input currents making it ideal for applications such as MOS, CMOS, and low power logic interfacing or RS232C data transmission systems. Each OLH 400 has a light emitting diode and an integrated photodiode-darlington detector IC mounted and coupled in a custom hermetic TO5 package providing 1000 Vdc electrical isolation between input and output.

Type	OLH400
Manufacturer	ISOLINK
Function	Optocoupler
Package	TO5
Date Code	1048
Sample size	16 parts (15 + 1 control sample)

3.2 Procurement information

75 parts OLH400 were delivered by ISOLINK through its French representative EUROMIP.

3.3 External view

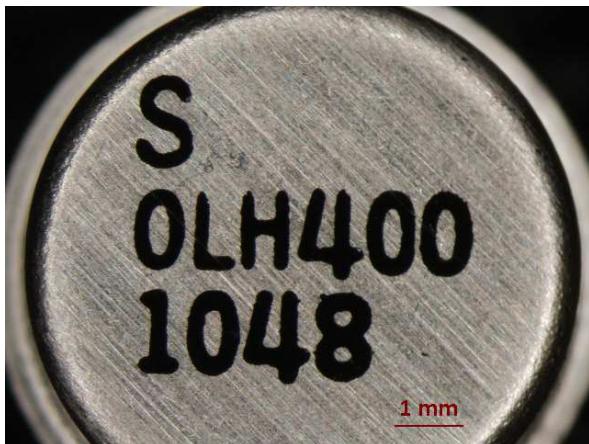


Figure 1: package marking

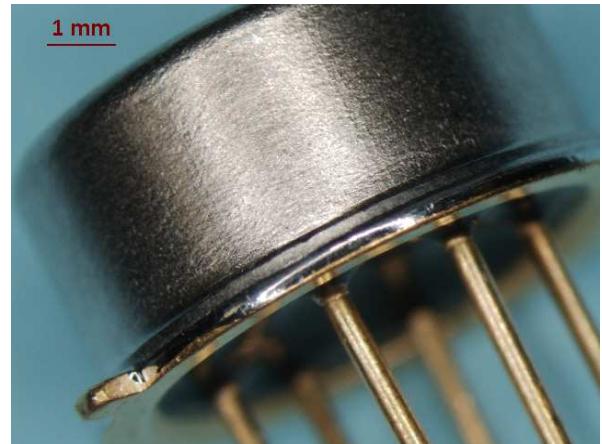


Figure 2: package view

3.4 Internal view

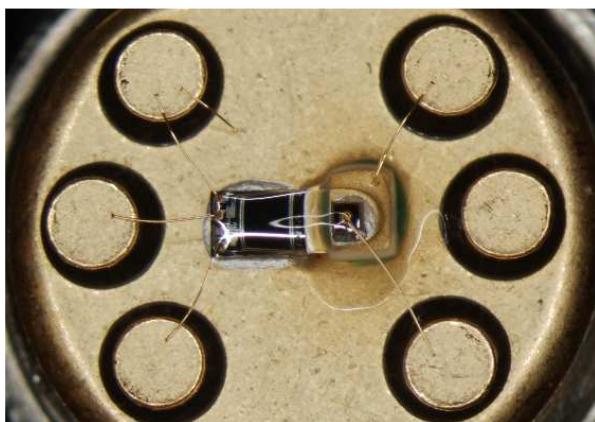
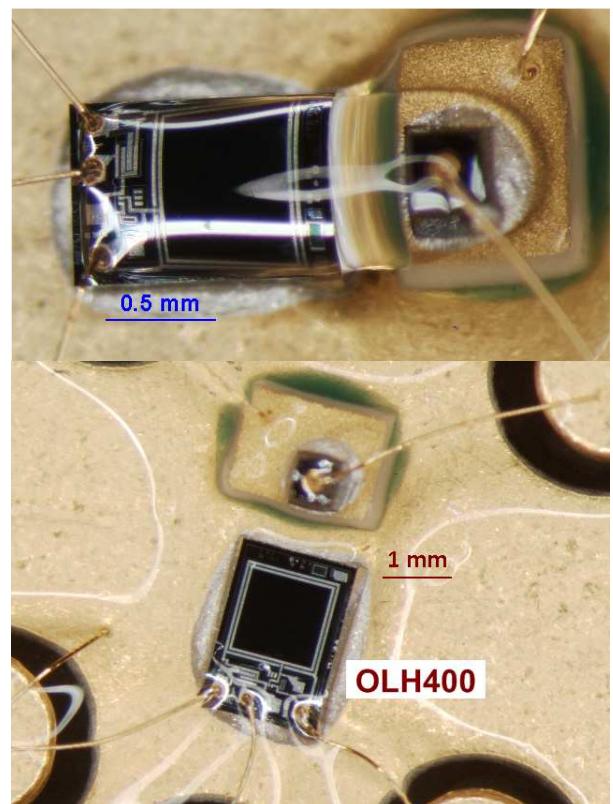


Figure 3: view of LED and integrated photodiode-darlington detector IC



3.5 Serialization

Each part is serialized to enable pre and post test identification and comparison.

Serial Number	Control sample	Test samples														
Serialization	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
	Ref	Bias1	Bias1	Bias1	Bias1	Bias1	Bias1	Bias2	Bias2	Bias2	Bias2	OFF	OFF	OFF	OFF	OFF

4 IRRADIATION MEANS AND CONDITIONS

4.1 UCL irradiation facility (Belgium)

Gamma irradiations are performed with Cobalt 60 source. Gamma emitted radiation energies are 1.17 and 1.33 MeV. Dose rates is equal 15 kRad(Si) / h at the source centre . Moreover the irradiation chamber is a cylindrical room with a radius of 2m. Then dose rate usable vary from 1.8 kRad(Si) / h to 80 Rad(Si) / h for normal irradiation positions and direct field.



4.2 Dose measurement

Alanine dosimeters are used for each test set up to control Total Ionizing Dose.

4.3 Experimental conditions

An Accumulated dose of 200 krad(Si) of ^{60}Co is required [AD2] for this TID (Total Ionizing Dose) evaluation test.

The test devices have been exposed to the following Dose rate:

	Step1	Step2	Step3	Step4	Step5	Step6	Step7	Step8
Accumulated dose krad(Si)	10	19	49	65	101	130	152	203
Dose rate (Si)/h	36	36	36	36	310	310	310	310

Two annealing steps are performed after Co60 irradiation:

Duration (h)	24	168
Temperature (°C)	25	100

5 ELECTRICAL TESTS

Electrical parameters to be measured in pre and post exposure tests are described in the following table. Electrical tests are performed on each part using the test set-up hereunder. All required data are recorded for each device. Test conditions and limits are given in the applicable irradiation test plan [AD2] and shown hereafter.

5.1 Test set-up

TEST BOARD	TRAD/CT1/E/OPTO/ZIP14/BR/1108
TEST PROGRAM	OLH400_TE_XXX1_B1_V10.llb

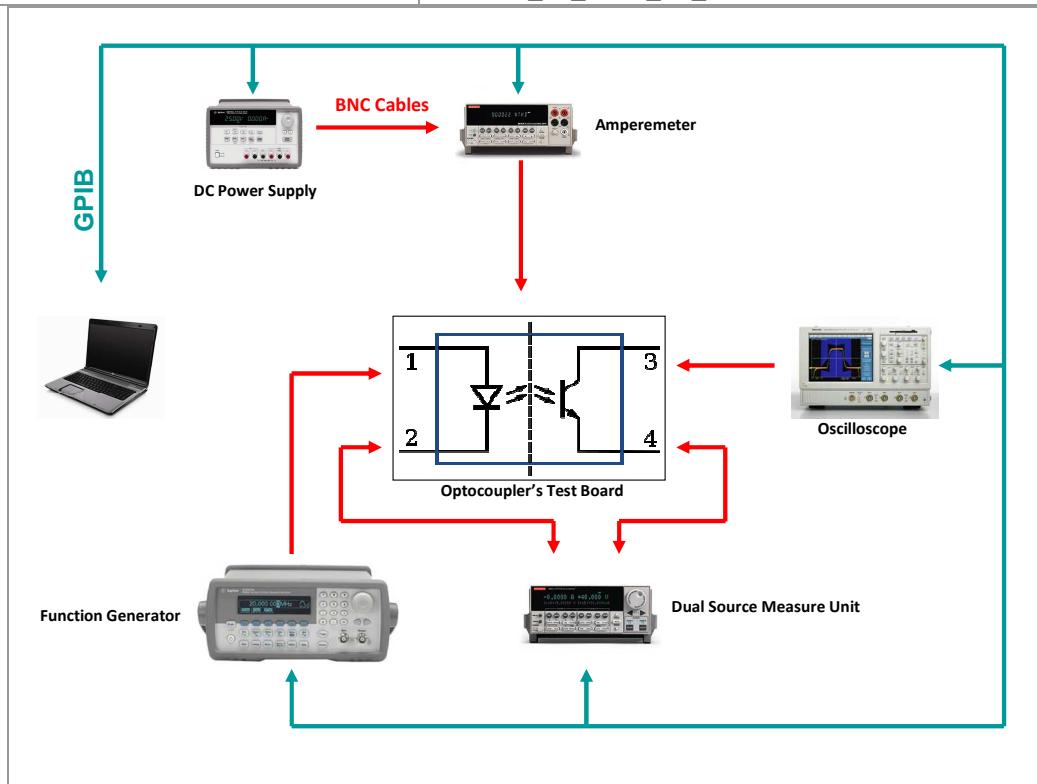


Figure 4: test principle

5.2 Test configuration

Samples were exposed to irradiation in three different modes - two on-modes (Figure 5 and Figure 6) and one off-mode (all terminal leads short-circuited) –

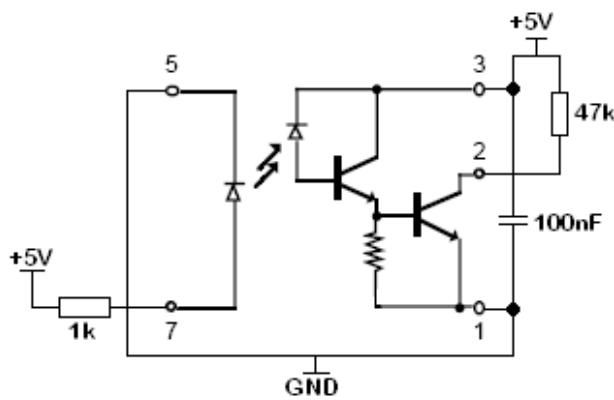


Figure 5: ON bias1

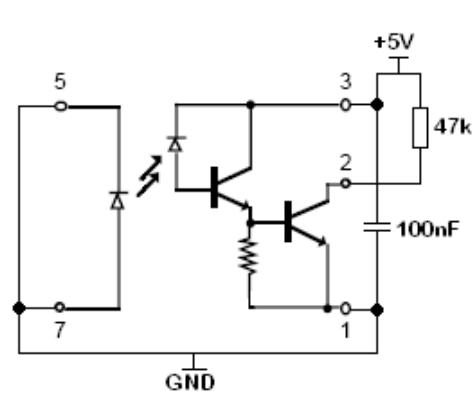


Figure 6: ON bias2

5.3 Electrical parameters

PARAMETER	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Logic Low Output Voltage	V_{OL1}	$I_F=0.5$ $\text{mA}, I_{OL}=1.5\text{mA}, V_{CC}=4.5\text{V}$		0.4	V
	V_{OL2}	$I_F=5 \text{ mA}, I_{OL}=10\text{mA}, V_{CC}=4.5\text{V}$		0.4	V
Logic High Output Current	I_{OH}	$I_F=0\text{mA}, V_O=V_{CC}=18\text{V}$		250	μA
Logic Low Supply Current	I_{CCL}	$I_F=1.6\text{mA}, V_{CC}=18\text{V}$		2	mA
Logic High Supply Current	I_{CCH}	$I_F=0\text{mA}, V_{CC}=18\text{V}$		40	μA
Input Forward Voltage	V_F	$I_F=1.6\text{mA}$		2	V
Input Reverse Breakdown Voltage	B_{VR}	$I_R=10 \mu\text{A}$	3		V
Propagation Delay Time Logic High to Low	t_{PHL1}	$I_F=0.5\text{mA}, R_L=4.7 \text{ K}\Omega, V_{CC}=5\text{V}$		100	μs
	t_{PHL2}	$I_F=5\text{mA}, R_L=680 \Omega, V_{CC}=5\text{V}$		10	μs
Propagation Delay Time Logic Low to High	t_{PLH1}	$I_F=0.5\text{mA}, R_L=4.7 \text{ K}\Omega, V_{CC}=5\text{V}$		60	μs
	t_{PLH2}	$I_F=5\text{mA}, R_L=680 \Omega, V_{CC}=5\text{V}$		30	μs
Current Transfer Ratio	CTR1	$I_F=1.6 \text{ mA}, V_O=0.4\text{V}, V_{CC}=4.5\text{V}$	300		%
	CTR2	$I_F=0.16 \text{ mA}, V_O=0.4\text{V}, V_{CC}=5\text{V}$			%
	CTR3	$I_F=0.32 \text{ mA}, V_O=0.4\text{V}, V_{CC}=5\text{V}$			%
	CTR4	$I_F=1.6 \text{ mA}, V_O=0.4\text{V}, V_{CC}=5\text{V}$			%
	CTR5	$I_F=16 \text{ mA}, V_O=0.4\text{V}, V_{CC}=5\text{V}$			%
	CTR6	$I_F=1.6 \text{ mA}, V_O=0.4\text{V}, V_{CC}=20\text{V}$			%

Min/ Max values are those specified in the reference data-sheet [RD1].

Test measurements are performed at $25^\circ\text{C} \pm 10^\circ\text{C}$.

6 TEST HISTORY

Seven steps are defined [AD2]to determine the component degradation under ^{60}Co irradiation.

	Step1	Step2	Step3	Step4	Step5	Step6	Step7
Accumulated dose krad(Si)	10	20	50	100	120	150	200
Dose rate (Si)/h	36	36	36	36	310	310	310

Due to irradiation facility maintenance, between Step 3 and Step 4 (50 krad(Si) and 100 krad(Si)), tests were stop for 48 hours. Total Ionizing Dose was estimated at 65 krad(Si). During this time period, parts were stocked in a cold chamber at -30°C .

7 SUMMARY RESULTS

Only parameters with applicable test limits are shown hereunder.

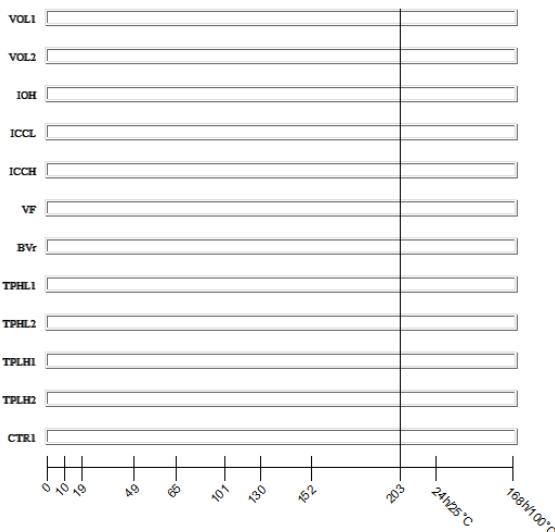


Figure 7: ON Bias 1

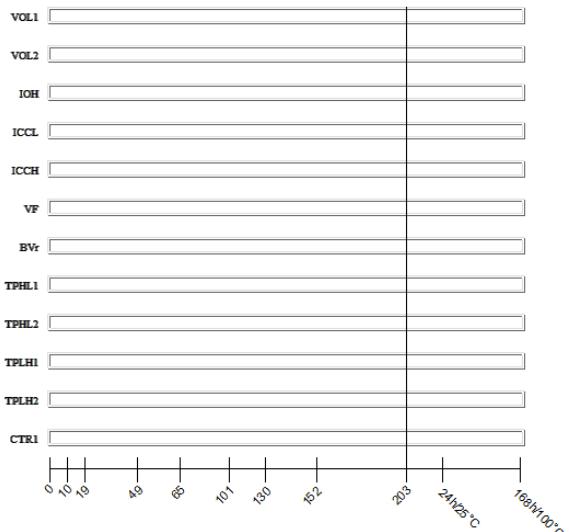


Figure 8 : ON Bias 2

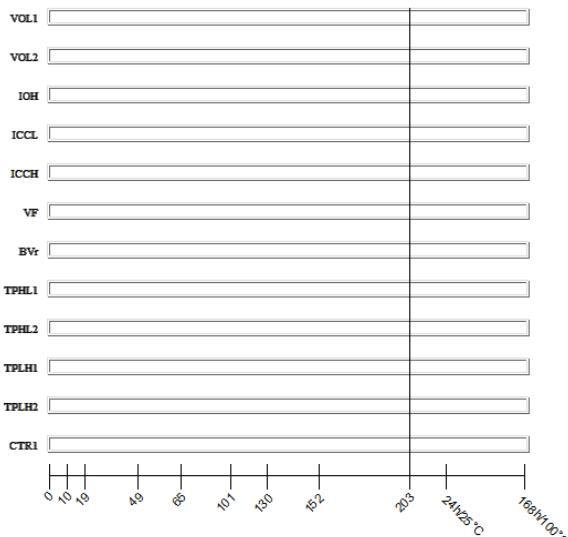


Figure 9: OFF Bias

- [] Within specification
- [] Transition
- [] Out of specification or parameter not measurable

All specified parameters [RD1] remain within the limits up to 203 kRad(Si).

8 CONCLUSION

Total Ionizing Dose steady-state irradiation test using Gamma ray was performed on OLH400 High Speed Hermetic Low Input-Current Optocoupler from ISOLINK up to 200krad(Si) under three bias conditions.

The results indicate that:

- All parameters are within specified values at total dose level.
- Average drift current transfer ratio function of the Bias condition and CTR configuration are described in the next Figure:

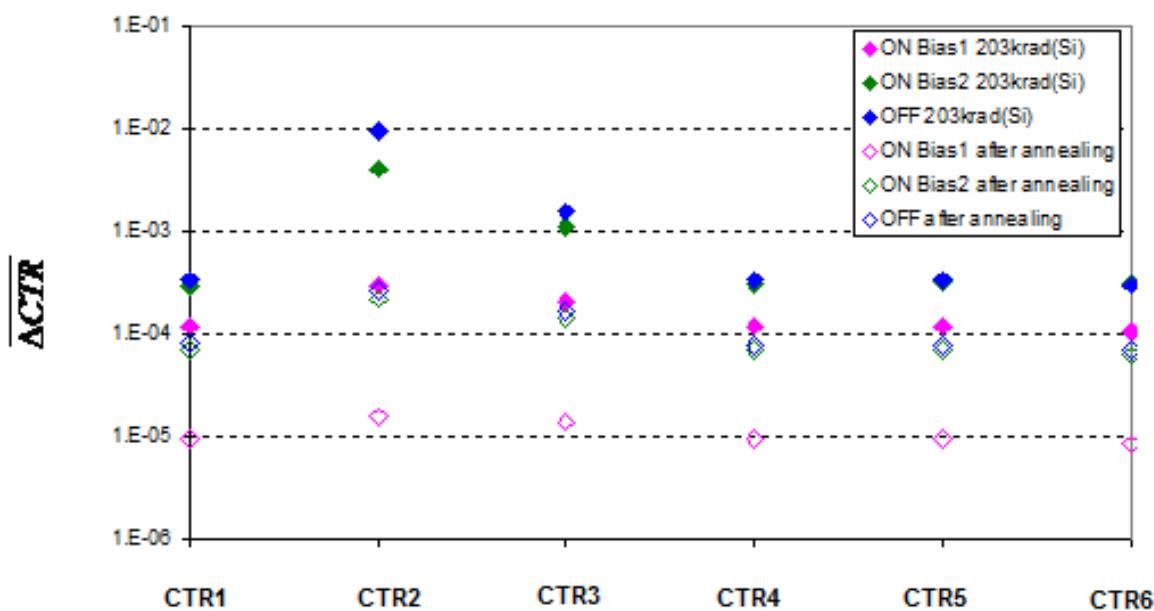


Figure 10: Average drift current transfer ratio function of the Bias condition and CTR configuration

- The least sensitive configuration at 203 krad(Si) total dose is the CTR6 condition ($I_F=1.6$ mA, $V_0=0.4V$, $V_{CC}=20V$)
- Conversely, CTR2 ($I_F=0.16$ mA, $V_0=0.4V$, $V_{CC}=5V$) exhibits the greatest parameter degradation up to 203krad (Si) total dose.
- ON Bias1 configuration is the least sensitive configuration for all CTR conditions.
- OFF mode is the most sensitive configuration.
- Moreover CTR1 ($I_F=1.6$ mA, $V_0=0.4V$, $V_{CC}=4.5V$), which is the only CTR configuration for which specification limits are indicated in the data-sheet, remain within this limit at total dose level.

As shown in previous figure, after annealing, average drift Current Transfer Ratio decrease.

9 DETAILED TESTS RESULTS

The pre and post radiation test results are shown graphically in the following pages (9-2 to 9-35). The data is displayed in the following tables and graphs.

These graphs show parameter's shifts observed during the total ionizing dose sequence. The Control sample results are shown on each graph (black curve).

When available in the device data-sheet/specification, the maximum/minimum/typical values are also shown (red dotted line).

The tables include drift calculation between each measurement step and the "0" kRad(Si) step.

For CTR values, the formula used is:

$$\text{Drift} = \frac{1}{\text{measurement (X kRad(Si))}} - \frac{1}{\text{measurement (0 kRad(Si))}}$$

For other parameters, the formula used is:

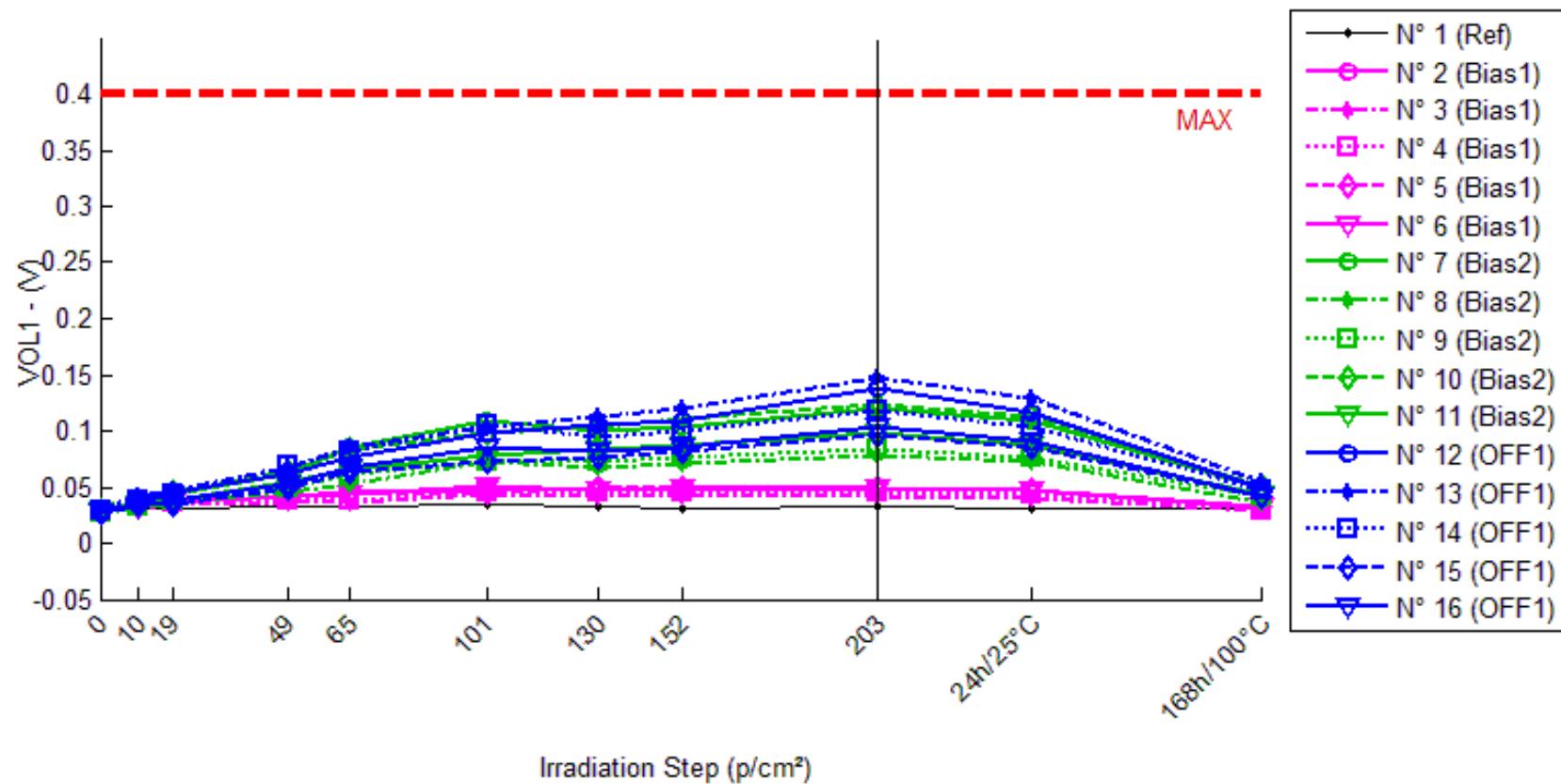
$$\text{Drift value} = \text{measurement (X kRad(Si))} - \text{measurement (0 kRad(Si))}$$

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9. TPHL2	18
10. TPLH1	20
11. TPLH2	22
12. CTR1	24
13. CTR2	26
14. CTR3	28
15. CTR4	30
16. CTR5	32
17. CTR6	34

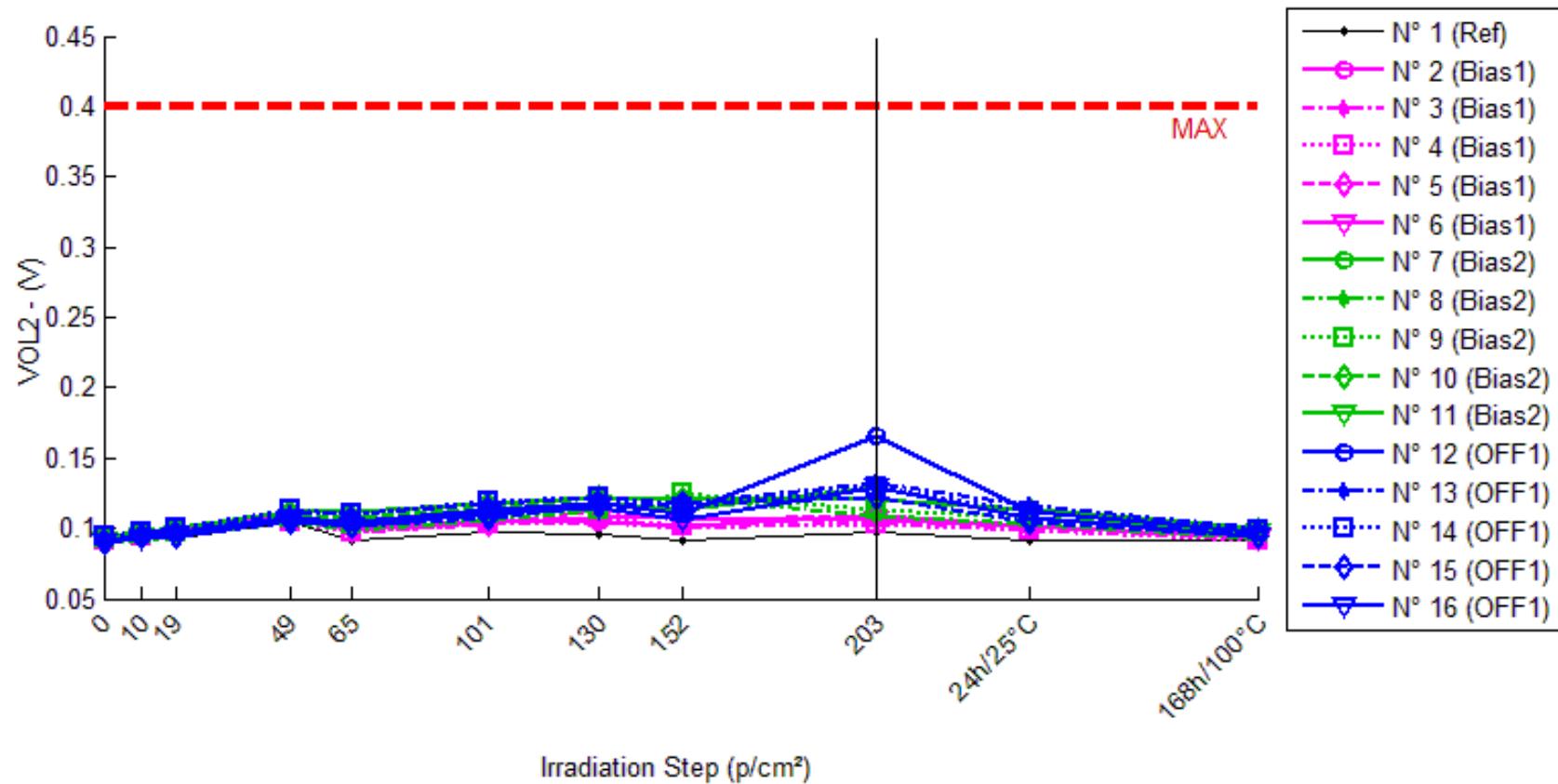
1. VOL1

Ta=25°C; If = 0.5 mA; IOL = 1.5 mA; Vcc = 4.5 V



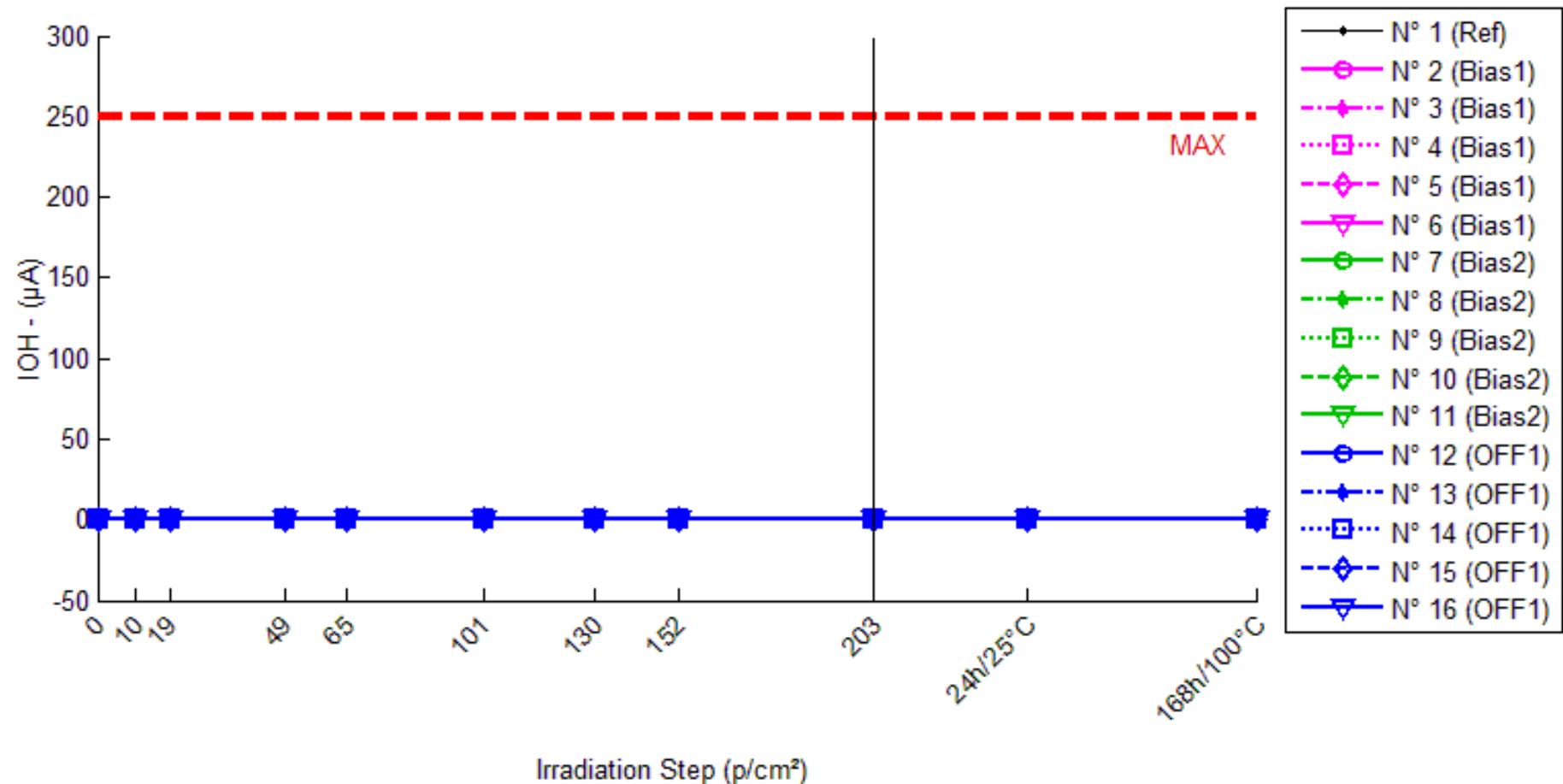
2. VOL2

T_a=25°C; I_f = 5 mA; I_{OL} = 10 mA; V_{cc} = 4.5 V



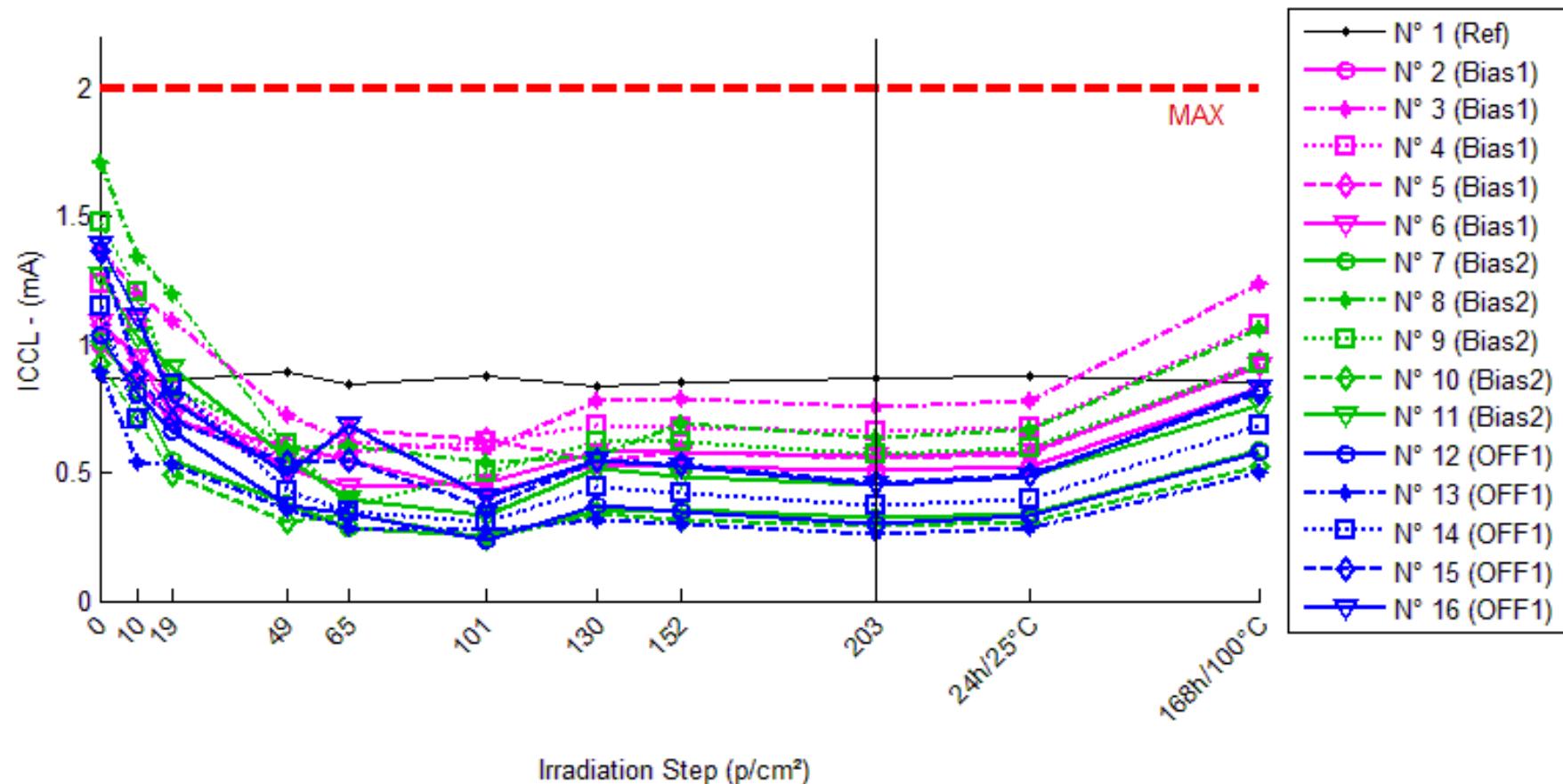
3. IOH

T_a=25°C; If = 0; V_O = V_{cc} = 18 V



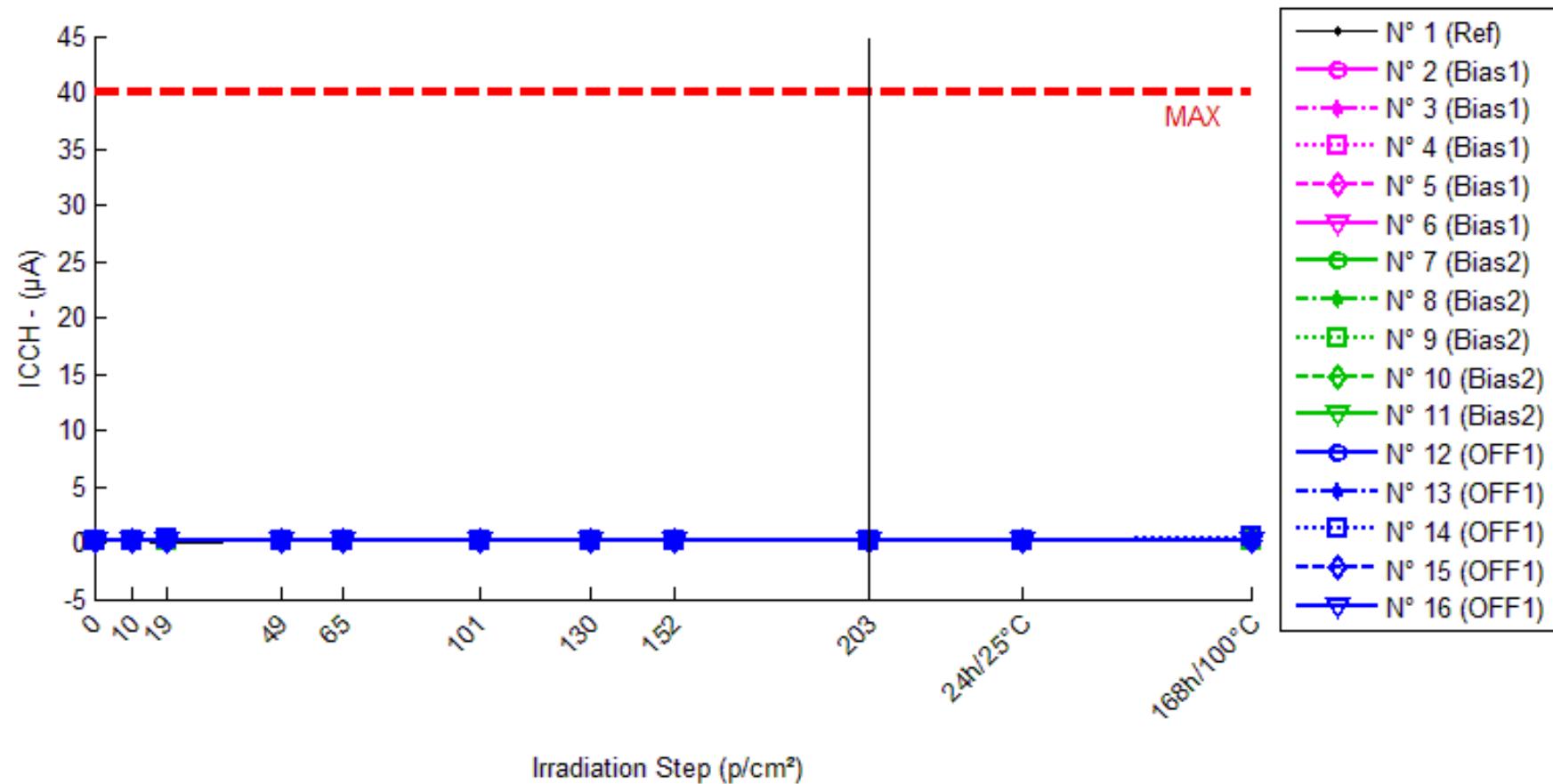
4. ICCL

T_a=25°C; I_f = 1.6 mA; V_{cc} = 18 V



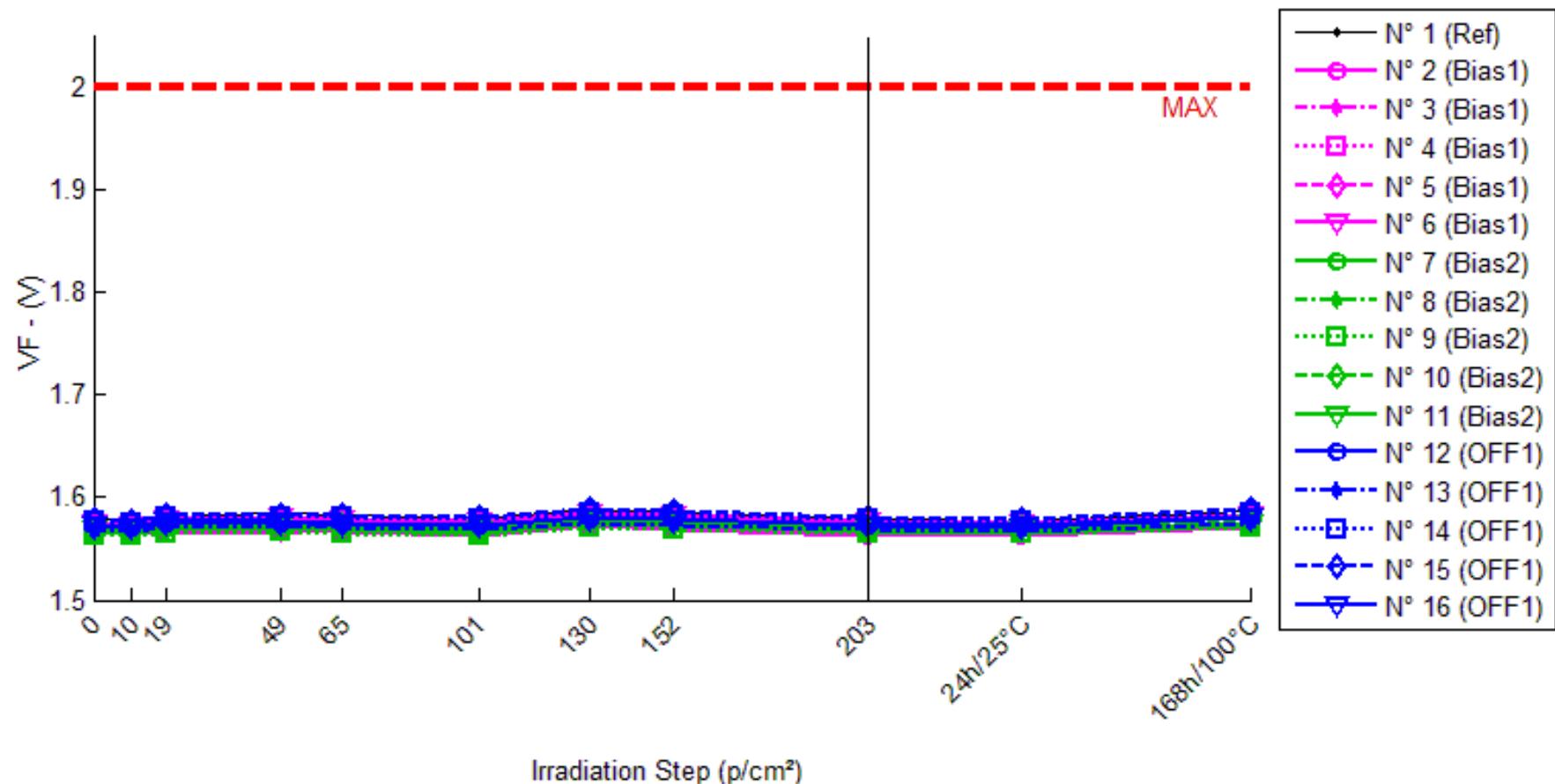
5. ICCH

T_a=25°C; If = 0; V_{cc} = 18 V



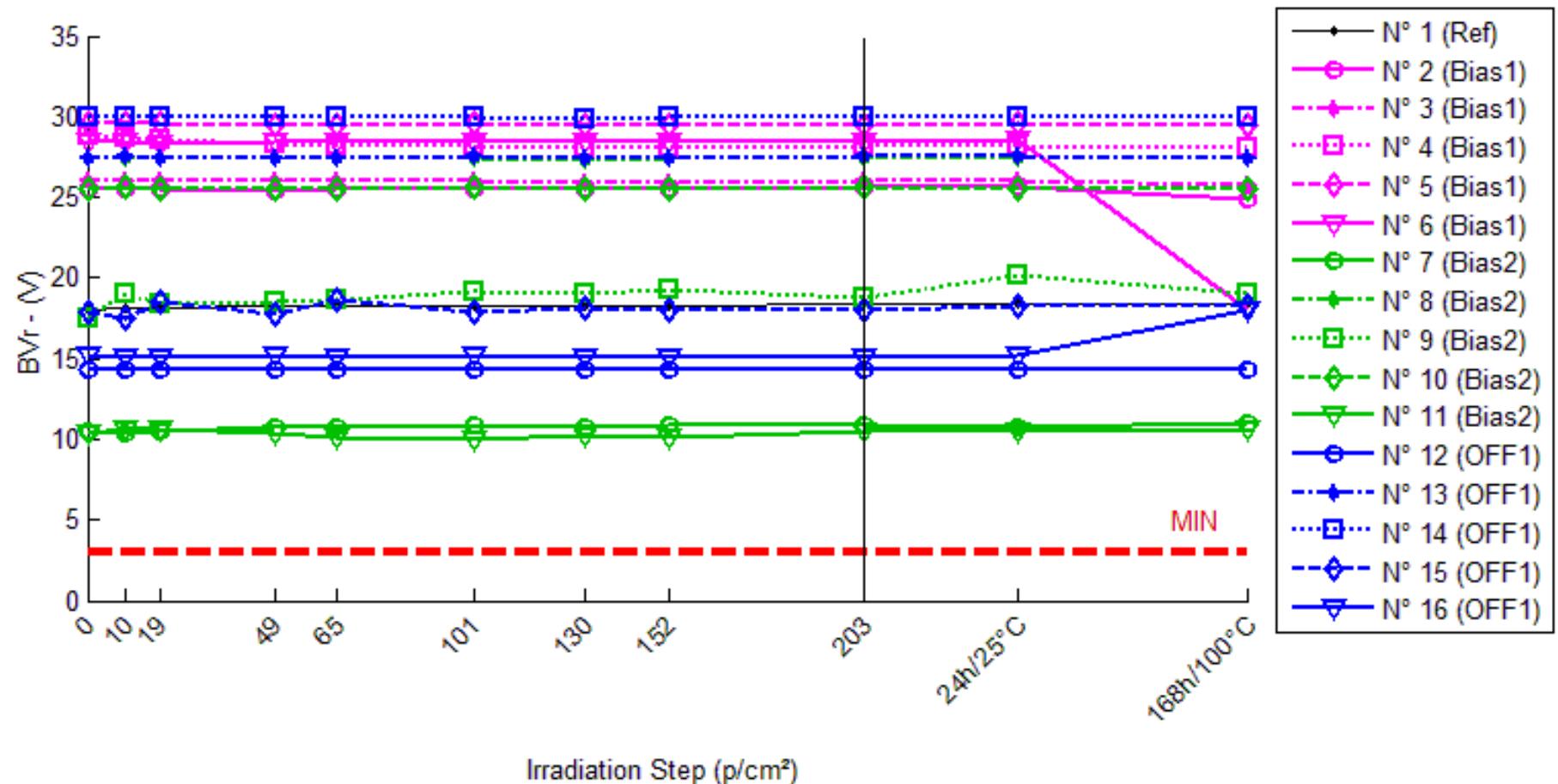
6. VF

T_a=25°C; If = 1.6 mA



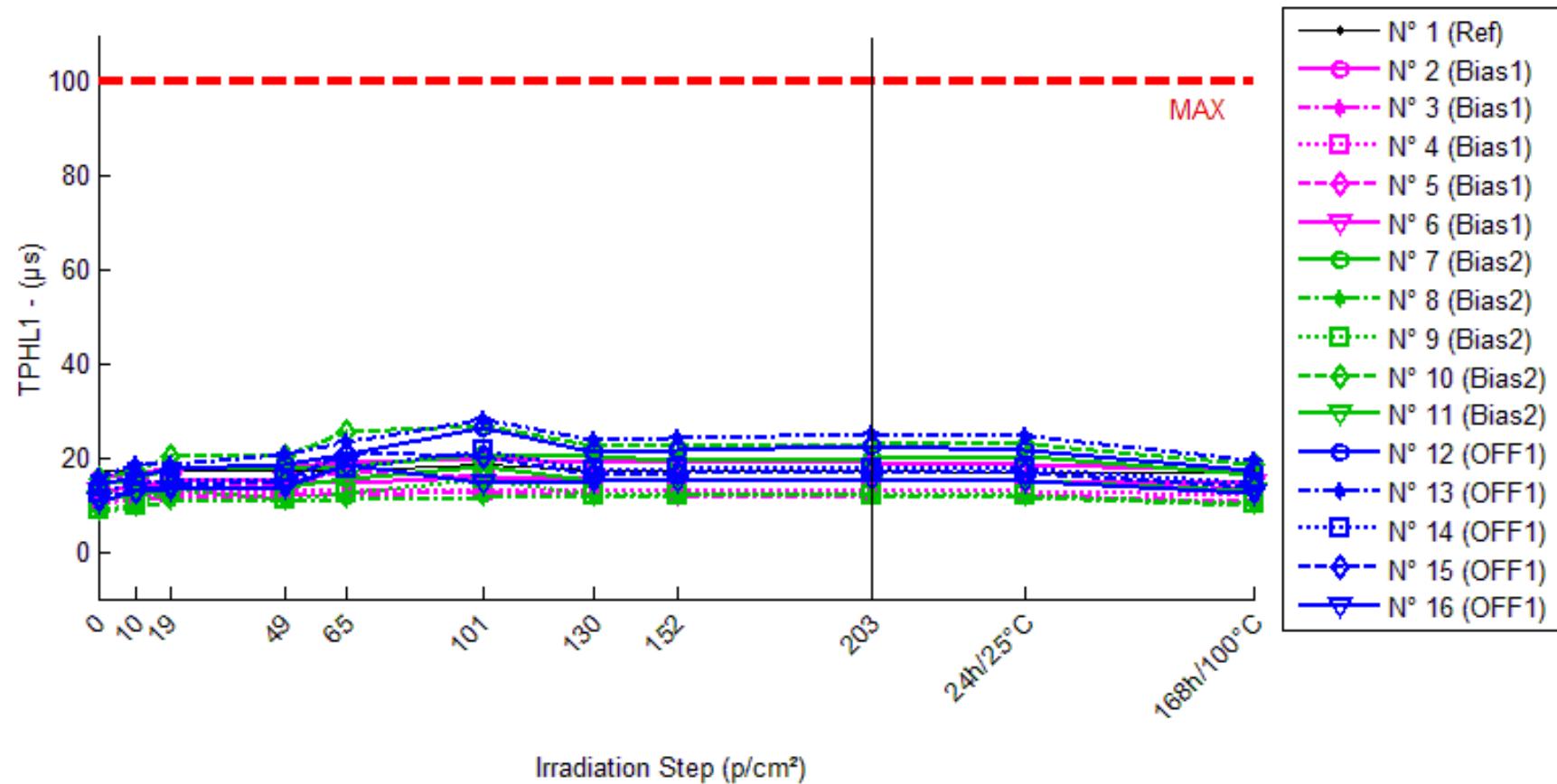
7. BV_r

T_a=25°C; I_r = 10 µA



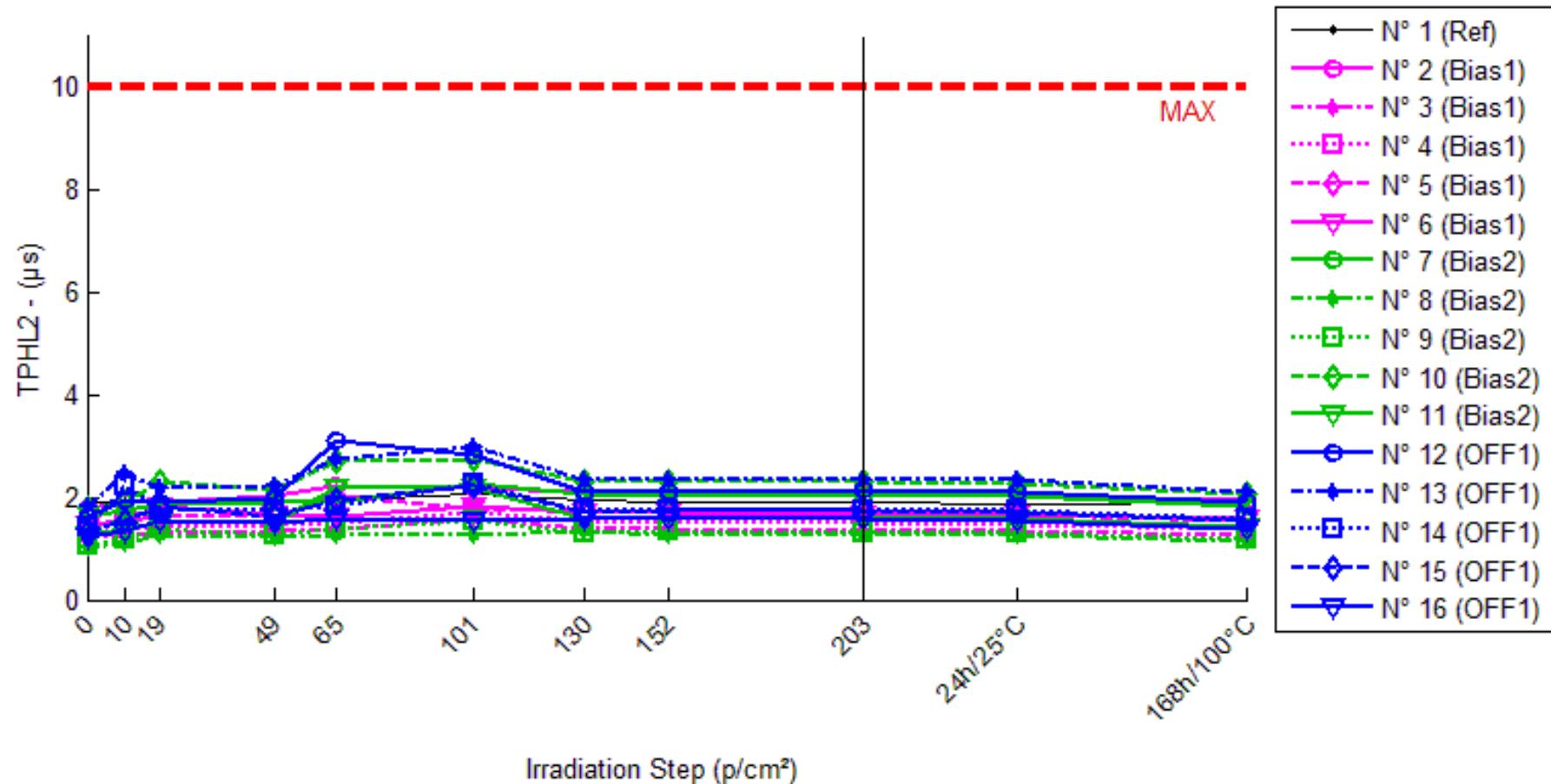
8. TPHL 1

T_a=25°C; I_f = 0.5 mA; R_L = 4.7 kOhms; V_{cc} = 5 V



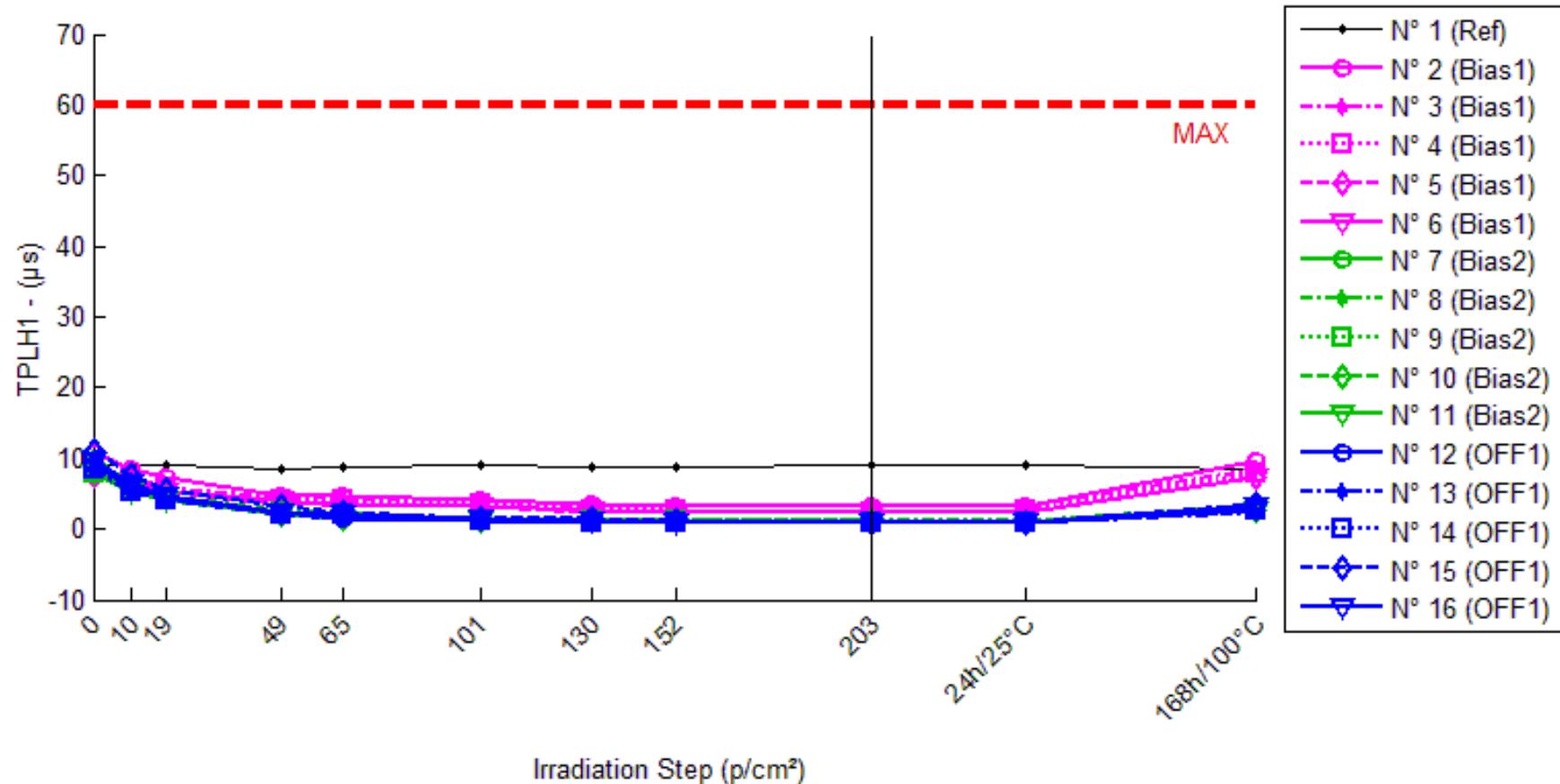
9. TPHL2

Ta=25°C; If = 5 mA; RL = 680 Ohms; Vcc = 5 V



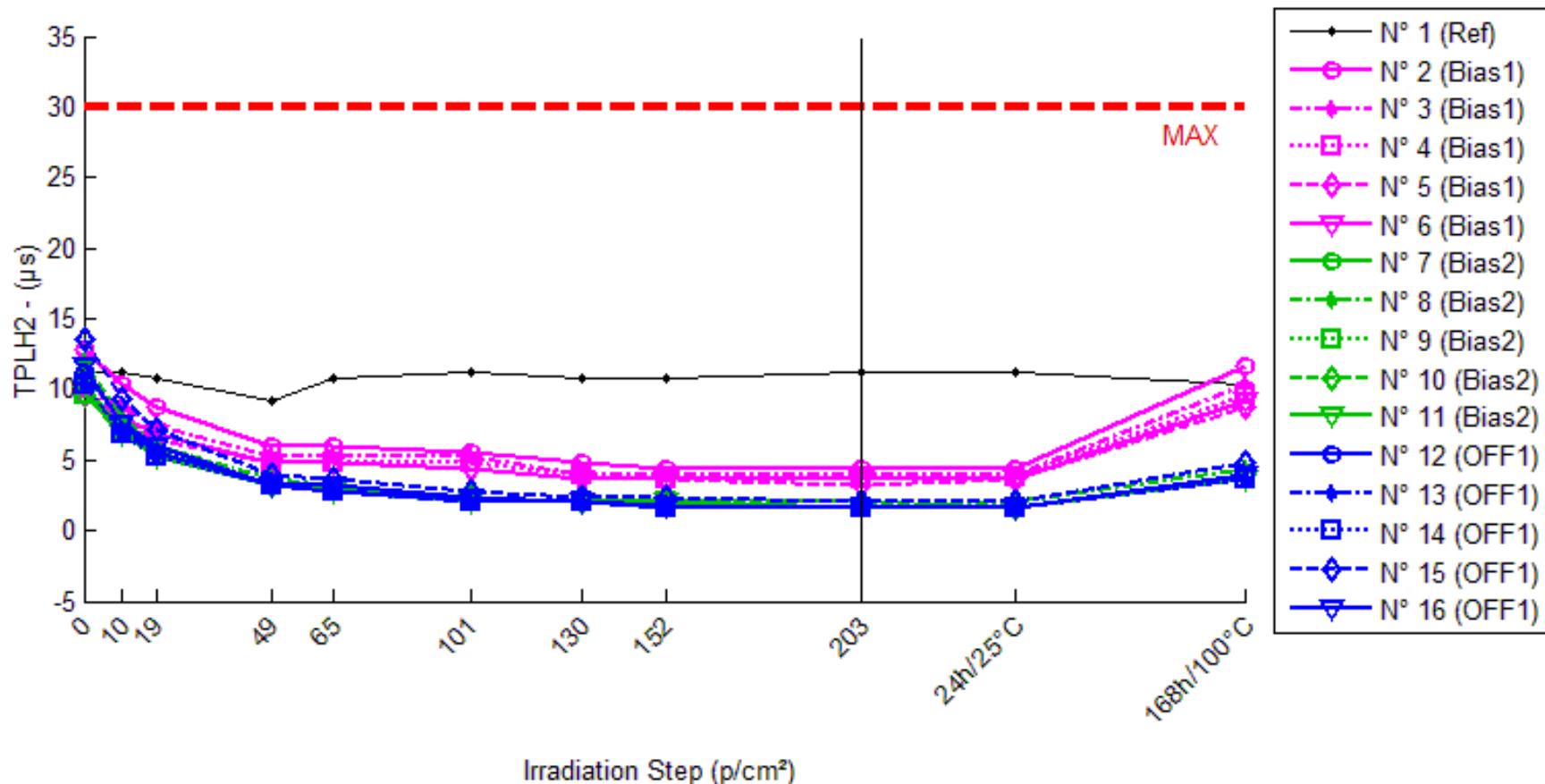
10.TPLH1

T_a=25°C; I_f = 0.5 mA; R_L = 4.7 kOhms; V_{cc} = 5 V



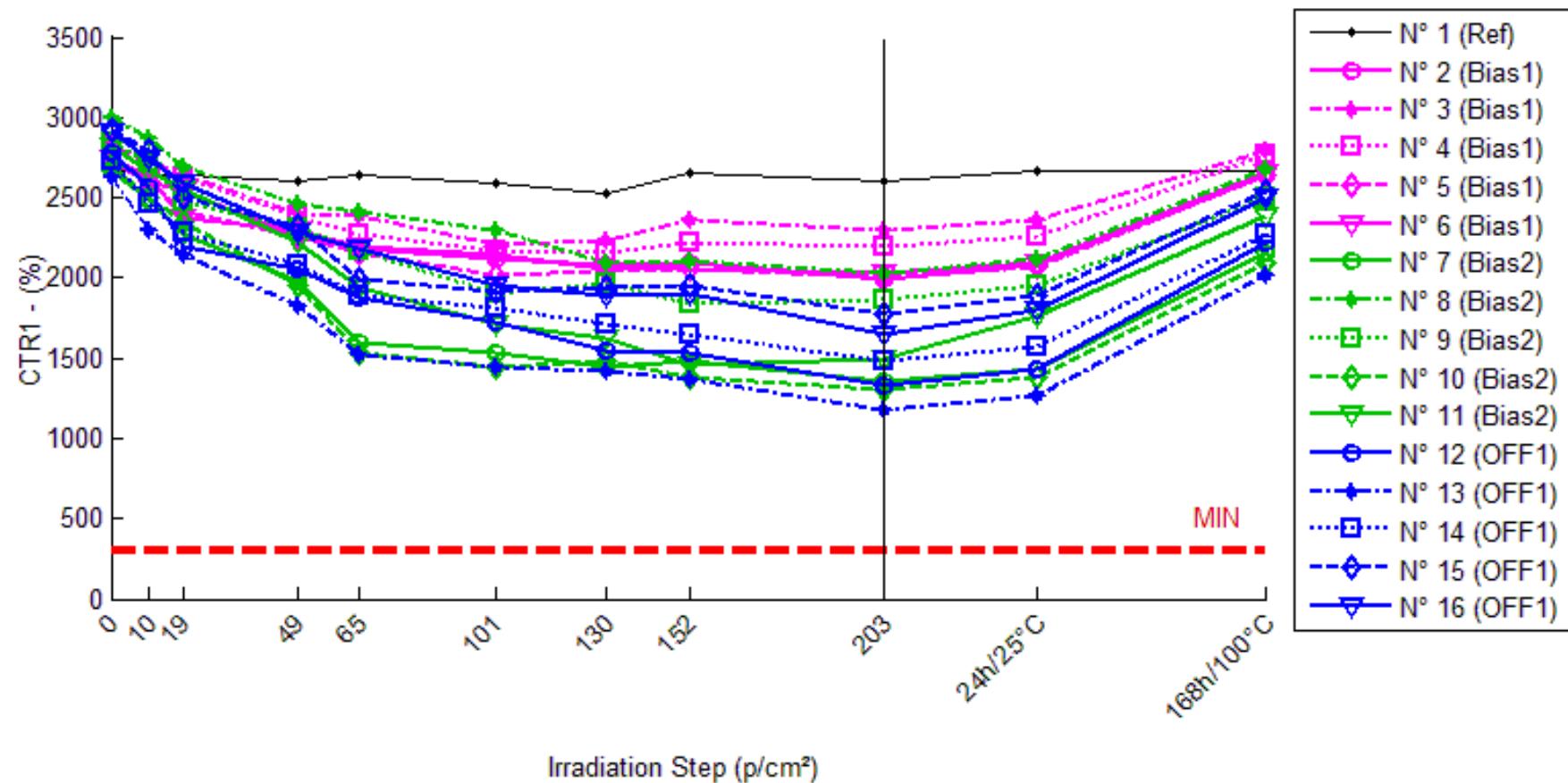
11.TPLH2

Ta=25°C; If = 5 mA; RL = 680 Ohms; Vcc = 5 V



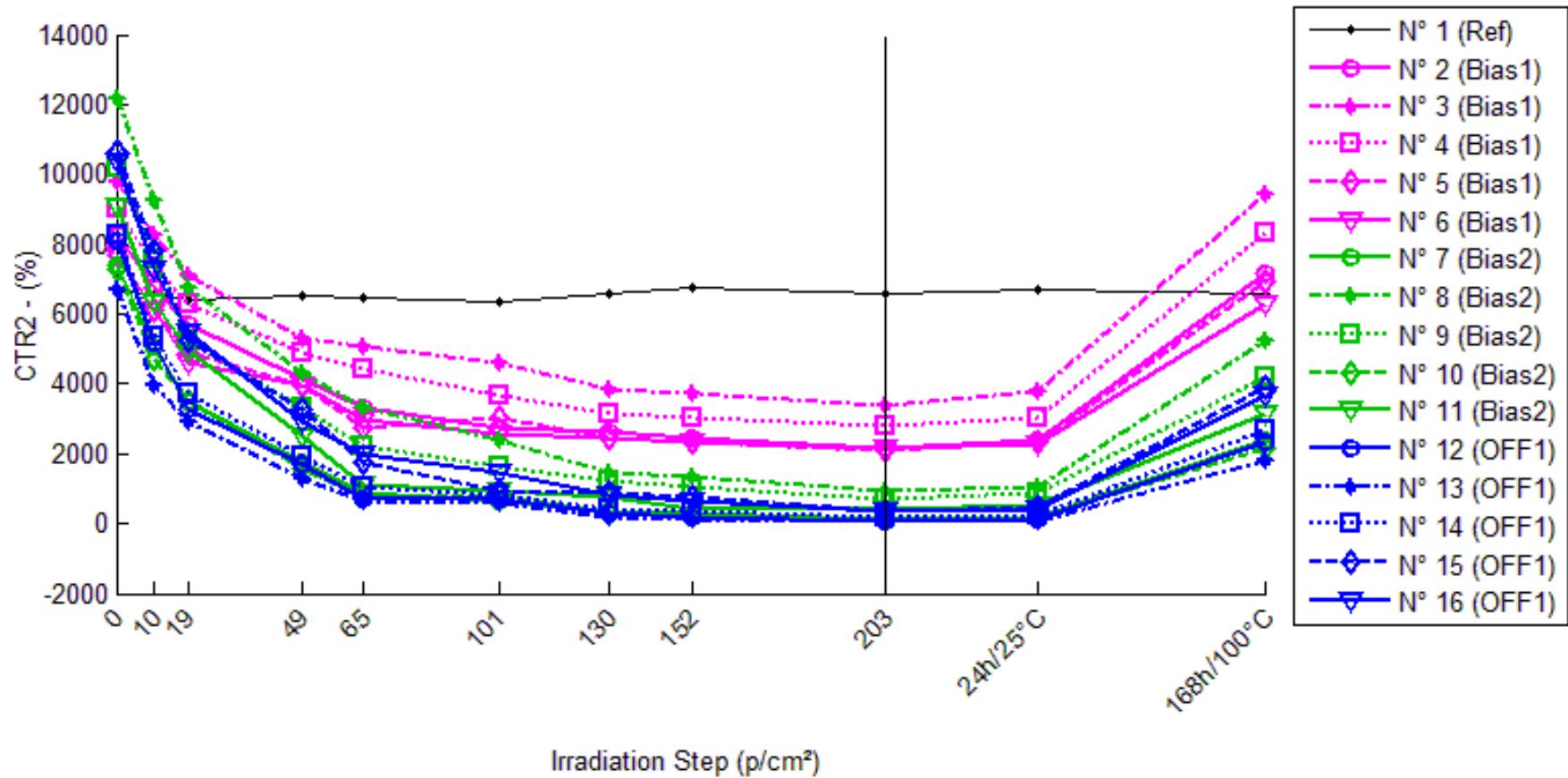
12.CTR1

T_a=25°C; I_f = 1.6 mA; V_o = 0.4 V; V_{cc} = 4.5 V



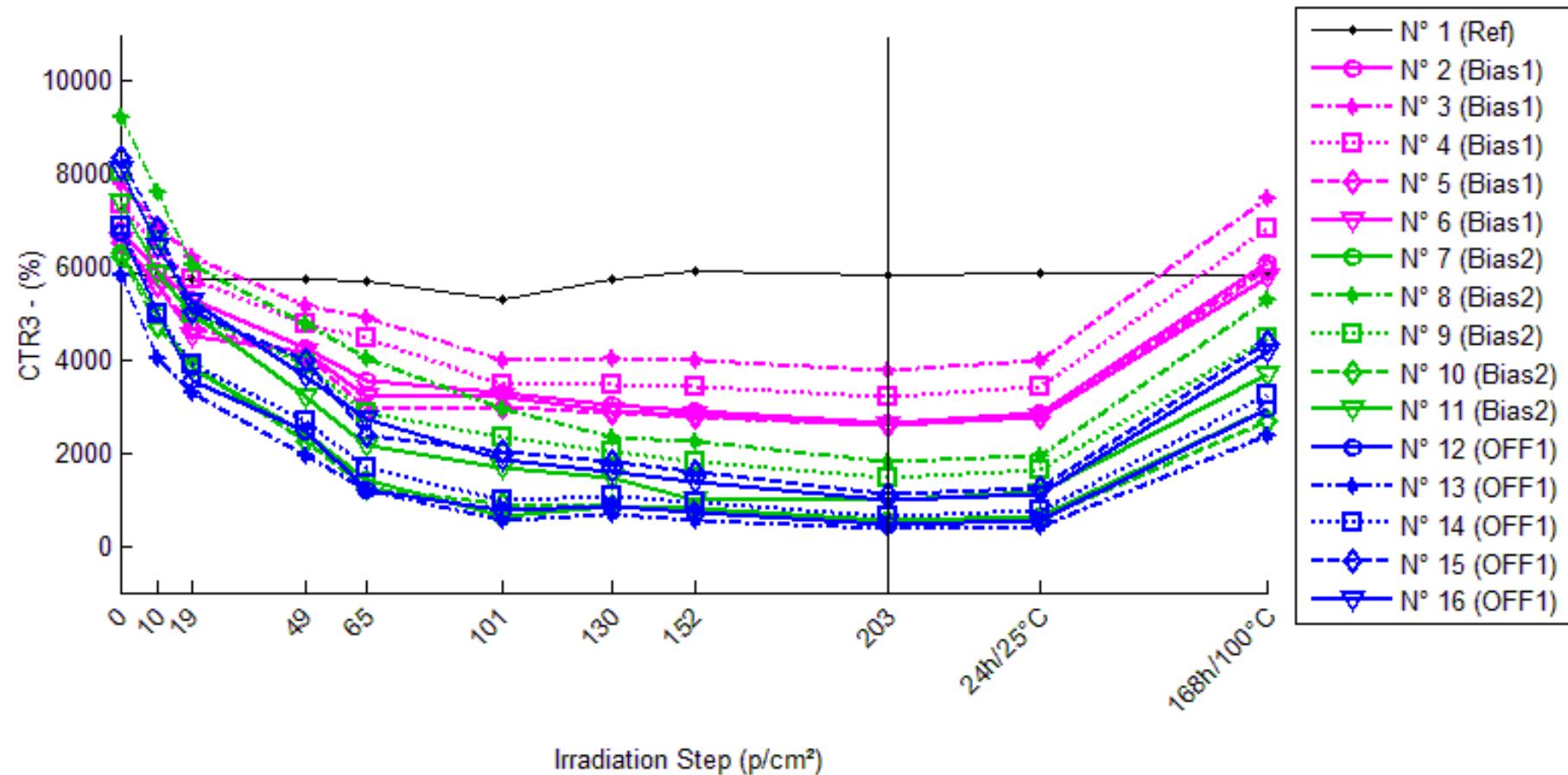
13.CTR2

Ta=25°C; If = 0.16 mA; Vo = 0.4 V; Vcc = 5 V



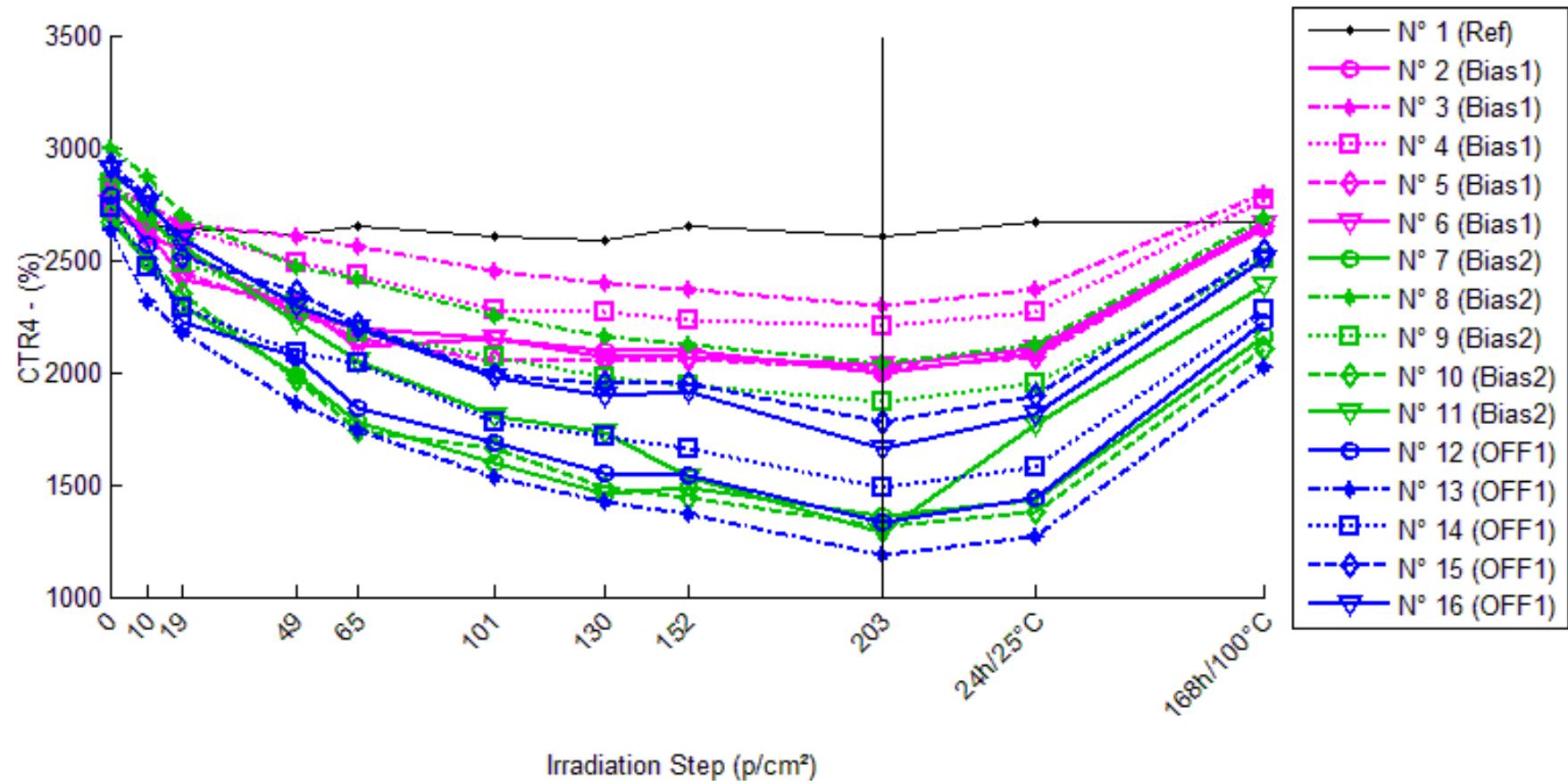
14. CTR3

Ta=25°C; If = 0.32 mA; Vo = 0.4 V; Vcc = 5 V



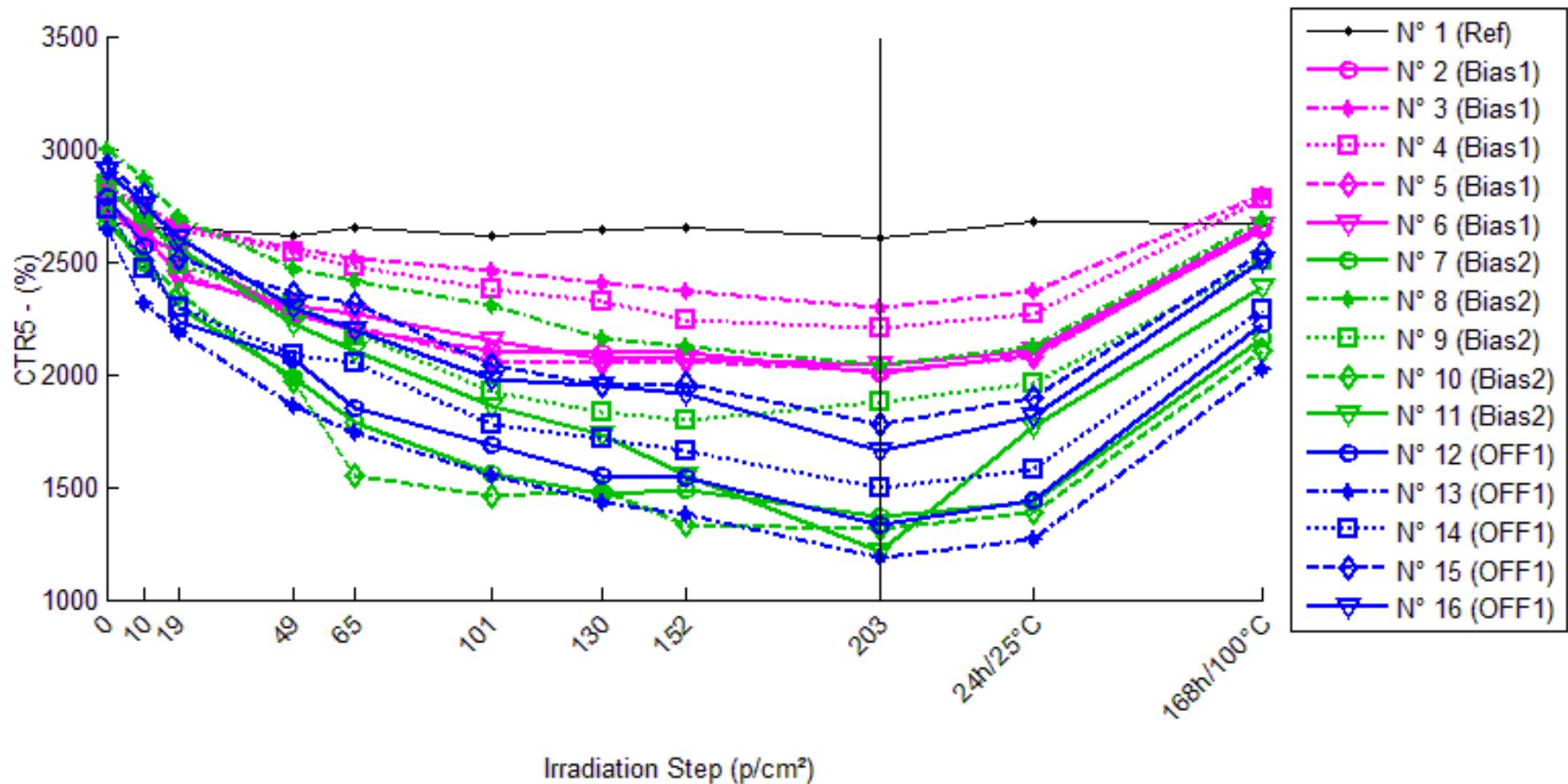
15. CTR4

Ta=25°C; If = 1.6 mA; Vo = 0.4 V; Vec = 5 V



16. CTR5

Ta=25°C; If = 16 mA; Vo = 0.4 V; Vcc = 5 V



17. CTR6

Ta=25°C; If = 1.6 mA; Vo = 0.4 V; Vec = 20 V

